## Hermetic Infrared Emitting Diode

OP215, OP216



#### Features:

- Hermetically sealed package
- Mechanically and spectrally matched to other OPTEK devices
- Designed for direct mount to PCBoard
- Enhanced temperature range
- Excellent coupling efficiency



### **Description:**

Each **OP215** and **OP216** device is an 890 nm gallium aluminum arsenide infrared emitting diode (GaAlAs), mounted in a hermetically sealed "pig tale" package with an enhanced temperature range and a narrow irradiance pattern that provides high on-axis intensity for excellent coupling efficiency. These devices offer significantly higher power output than GaAs at equivalent drive currents and have a wavelength that is matched to silicon's peak response. Their small package size permits high device density mounting.

The OP216 series devices provide an additional mounting tab connected to the Cathode/Case.

All these LEDs are mechanically and spectrally matched to the OP300 series, OP516, OP600 series and OP640 series devices.

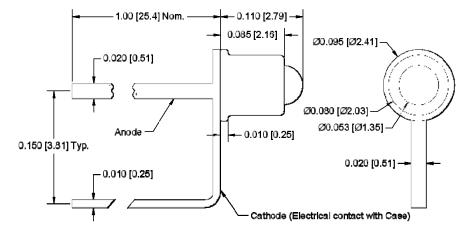
<u>Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data, and to Application Bulletin 202 for pill-type soldering to PCBoard.</u>

### Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

1		
lacktriangle	Pin #	LED
<b>T</b>	1	Anode
	2	Cathode
2		

Ordering Information					
Part Number		LED Peak Wavelength	Optical Power mW/ cm² (Min)	Total Beam Angle	
OP215A	OP216A		1.20		
OP215B	OP216B	890 mm	0.60	24°	
OP215C	OP216C	090 111111	0.30	24	
OP215D	OP216D		0.20		





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### **Electrical Specifications**

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)			
Storage Temperature Range	-65°C to +150°C		
Operating Temperature Range	-65°C to +125°C		
Reverse Voltage	2.0 V		
Continuous Forward Current	100 mA		
Peak Forward Current (2µs pulse with 0.1% duty cycle)	1.0 A		
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)(2)</sup>		
Power Dissipation	150 mW <sup>(3)</sup>		

Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diod	le						
E <sub>E (APT)</sub> <sup>(3)</sup>	Apertured Radiant Incidence OP216A OP216B OP216C OP216D	1.20 0.60 0.30 0.20	-	-	mW/cm²	I <sub>F</sub> = 50 mA <sup>(4)</sup>	
V <sub>F</sub>	Forward Voltage	-	-	1.80	V	I <sub>F</sub> = 50 mA	
$I_{R}$	Reverse Current	-	-	100	μA	V <sub>R</sub> = 2.0 V	
Р	Wavelength at Peak Emission	-	890	-	nm	I <sub>F</sub> = 10 mA	
В	Spectral Bandwidth between Half Power Points	-	80	-	nm	I <sub>F</sub> = 10 mA	
Δ /ΔΤ	Spectral Shift with Temperature	-	+0.18	-	nm/°C	I <sub>F</sub> = Constant	
НР	Emission Angle at Half Power Points	-	24	-	Degree	I <sub>F</sub> = 50 mA	
t <sub>r</sub>	Output Rise Time	-	500	-	ns	I <sub>F(PK)</sub> =100 mA, PW=10 μs, and D.C.=10.0 %	
t <sub>f</sub>	Output Fall Time	-	250	-	ns		

### Notes:

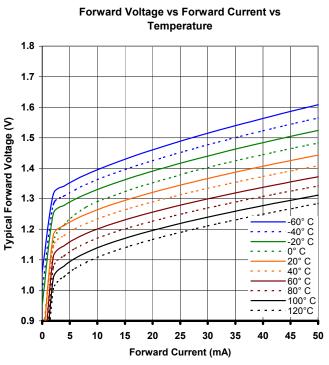
- 1. Refer to Application Bulletin 202 which reviews proper soldering techniques for pill-type devices.
- No clean or low solids. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
   Derate linearly 1.50 mW/° C above 25° C.
- 4. For OP216,  $E_{E(APT)}$  is a measurement using a 0.180" (4.57 mm) diameter apertured sensor placed 0.653" (16.59 mm) from the lens tip.  $E_{E(APT)}$  is not necessarily uniform within the measured area.

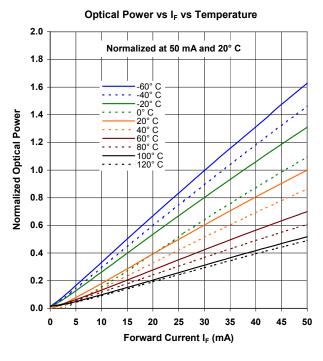
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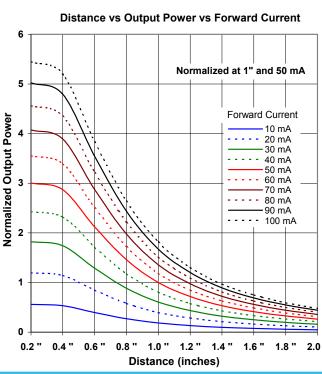


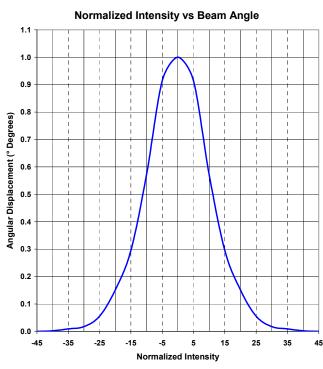


## Performance OP215 & OP216









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